

Si Photo Diode Chip--ORT-20120PD

1. Scope:

- The specification applies to PIN silicon photo diode chips.
- Type: ORT-20120PD

2. Structure:

- PIN planar type.
- Top (Anode) Side: aluminum (Al) alloy.
- Back (Cathode) Side: silver (Ag) alloy.

3. Size: (120mil×120mil)

- Chip size : $(3050\mu\text{m} \times 3050\mu\text{m}) \pm 40\mu\text{m}$
- Chip thickness : $220\mu\text{m} \pm 20\mu\text{m}$
- Active area : $(2794\mu\text{m} \times 2794\mu\text{m}) \pm 15\mu\text{m}$
- Pad size : $\Phi 190\mu\text{m} \pm 10\mu\text{m}$
- Pattern drawing: per fig. 1

4. Electro-Optical Characteristics:

(Ta=+25℃)

Parameter	Symbol	Test Condition	Min	Typ	Max	Unit
Forward voltage	V_F	$I_F=100\text{mA}$, $H=0$	0.5		1.3	V
Reverse Breakdown voltage	V_{BR}	$I_R=100\mu\text{A}$, $H=0$	35			V
Reverse Dark Current	I_D	$V_R=10\text{V}$, $H=0$			10	nA
Light Current	I_L	$V_R=5\text{V}$, Has $1\text{mw}/\text{cm}^2$, @ 940nm		175		μA
Peak Sensing wavelength	λ_P			940		nm
Junction Capacitance	C_J	$V_R=3\text{V}$, $F=1\text{MHz}$		27		pF

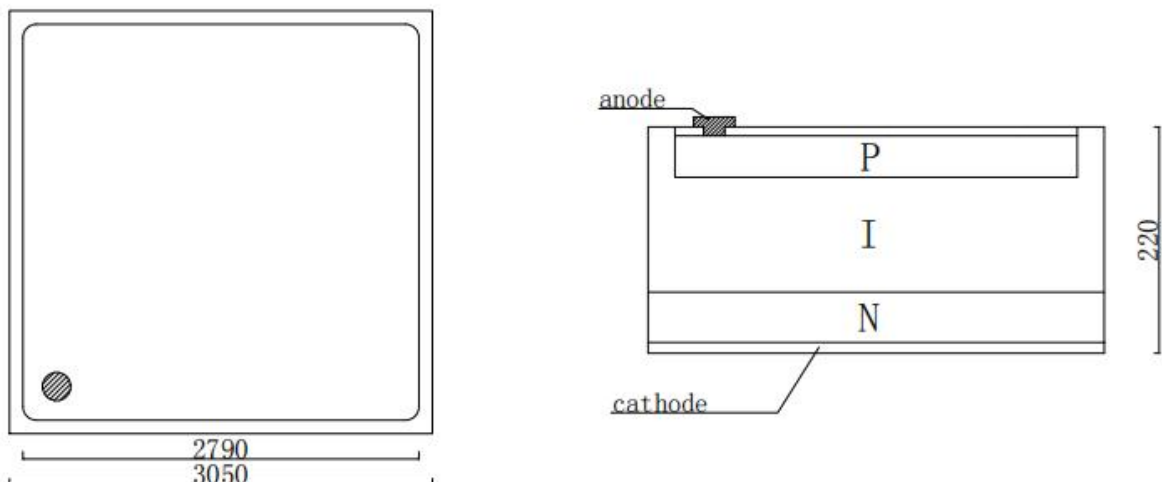


fig.1

5. Spectral Response

